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International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 : H01L 21/68 — A1

(11) International Publication Number: WO 99/50902

(43) International Publication Date: 7 October 1999 (07.10.99)

(21) International Application Number: PCT/US99/03211

(22) International Filing Date: 15 February 1999 (15.02.99)

(30) Priority Data:
09/050,476 30 March 1998 (30.03.98) US

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(81) Designated States: AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published
With international search report.

(54) Title: SEMICONDUCTOR WAFER PROCESSING TAPES

(57) Abstract

A semiconductor wafer processing tape includes a permanent backing and a layer of a nonpressure sensitive adhesive. The tapes are useful for wafer grinding and/or wafer dicing applications. The nonpressure sensitive adhesive includes a copolymer of at least one of a first monoethylenically unsaturated monomer, at least one of a second monoethylenically unsaturated monomer, and at least one copolymerizable nonionic cross-linking agent; wherein the second monoethylenically unsaturated monomer is reinforcing monomer having a homopolymer glass transition temperature higher than that of the first monoethylenically unsaturated monomer. A method of processing semiconductor wafers is also provided.